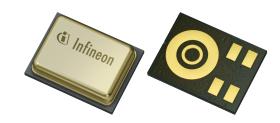


# AEC-Q103 qualified high performance digital XENSIV MEMS microphone









#### **Features**

- Dynamic range of 103dB for best speech performance
  - Signal to noise ratio of 67dB(A) SNR
  - <1% total harmonic distortions up to high SPL levels
  - Acoustic overload point at 130dBSPL
- AEC-Q103 qualification
- Close sensitivity and phase matching for use in arrays
- Flat frequency response with low frequency roll off and very fast analog to digital conversion speed for best ANC performance
- Digital PDM output
- Extended availability to match automotive design cycles

#### **Product validation**

Technology qualified for industrial applications Product qualified according to AEC-Q103-003

# **Potential applications**

- Hands free calling
- eCall
- Voice control
- Active noise cancellation / Road noise cancellation (ANC/RNC)
- · Siren detection
- Road condition detection

# **Ordering Information**

#### Table 1 Order information

Product name	Package	Marking	Ordering code
IM67D130A	PG-LLGA-5-1	IM67DA	SP005447450

#### **IM67D130A**

#### **AEC-Q103 qualified high performance digital XENSIV MEMS microphone**



## **Product description**

The device is designed for applications where low self-noise (high SNR), wide dynamic range, low distortions and a high acoustic overload point is required.

Infineon's Dual Backplate MEMS technology is based on a miniaturized symmetrical microphone design, similar as utilized in studio condenser microphones and results in high linearity of the output signal within a high dynamic range. The microphone distortion does not exceed 1% even up to very high sound pressure levels. With its low equivalent noise floor the microphone is no longer the limiting factor in the audio signal chain and enables higher performance of voice recognition algorithms.

The digital microphone ASIC contains an extremely low-noise preamplifier and a high-performance sigma-delta ADC. Different power modes can be selected in order to suit specific current consumption requirements.

The tight manufacturing tolerance, combined with the fact that each device is calibrated with an advanced Infineon calibration algorithm, results in small sensitivity and phase matching tolerances. This makes it a perfect device for beam forming arrays and multi-microphone applications.

# **IM67D130A**

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



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# **Table of contents**

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### AEC-Q103 qualified high performance digital XENSIV MEMS microphone



### 1 Typical performance characteristics

# 1 Typical performance characteristics

Test conditions: V<sub>DD</sub> = 1.8V, f<sub>CLK</sub> = 3.072 MHz, no load on DATA

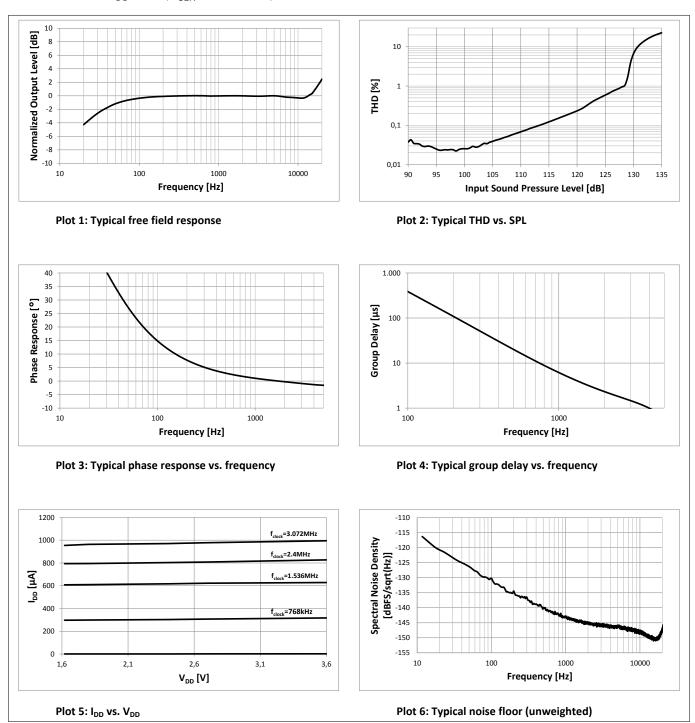


Figure 1 Typical performance characteristics

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



2 Block diagram

# 2 Block diagram

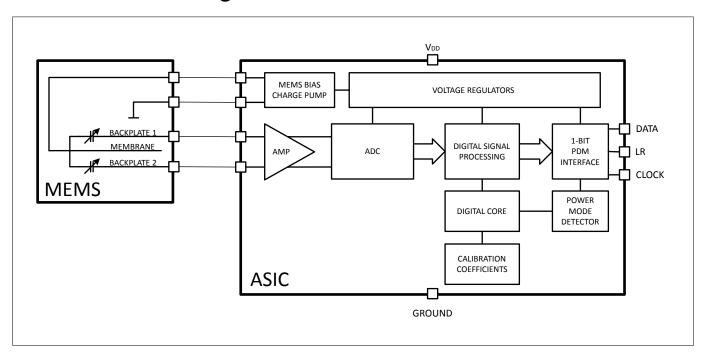


Figure 2 Block diagram

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



# 3 Pin configuration

# **3** Pin configuration

The figure below shows the pin configuration of the device

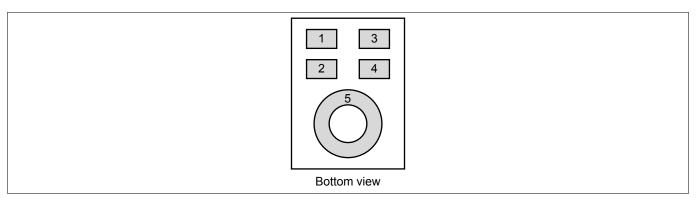


Figure 3 Pin configuration

Table 2 Pin configuration

Pin number	Name	Description
1	DATA	PDM data output
2	V <sub>DD</sub>	Power supply
3	CLOCK	PDM clock input
4	LR	PDM left/right select
5	GND	Ground

### AEC-Q103 qualified high performance digital XENSIV MEMS microphone



## **4 General product characteristics**

#### **General product characteristics** 4

#### **Acoustic characteristics** 4.1

Test conditions (unless otherwise specified in the table):  $V_{DD} = 1.8V \pm 0.1V$ ,  $f_{CLK} = 3.072MHz$ ,  $T_A = 25^{\circ}C \pm 5^{\circ}C$ , audio bandwidth 20Hz to 20KHz, LR pin grounded, no load on DATA,  $t_{CR} = t_{CF} = 9$ ns

Table 3 **Acoustic specifications** 

Parameter	Symbol	Values			Unit	Note or condition	
		Min.	Тур.	Max.			
Sensitivity	Sens	-37	-36	-35	dBFS	1kHz, 94 dBSPL, all operating modes	
Acoustic Overload Point	AOP	-	130	-	dBSPL	THD = 10%, all operating modes	
Signal to Noise Ratio, fCLK=3.072MHz	SNR	-	67	-	dB(A)	A-Weighted	
Signal to Noise Ratio, fCLK=2.4MHz	SNR <sub>M2</sub>	-	67	-	dB(A)	A-Weighted	
Signal to Noise Ratio, fCLK=1.536MHz	SNR <sub>M3</sub>	-	66	-	dB(A)	A-Weighted	
Signal to Noise Ratio, fCLK=768kHz	SNR <sub>LPM</sub>	-	64	-	dB(A)	20Hz to 8kHz bandwidth, A- Weighted	
Noise Floor, fCLK = 3.072MHz	NF	-	-103	-	dBFS(A)	A-Weighted	
Noise Floor - Mode2, fCLK = 2.4MHz	NF <sub>M2</sub>	-	-103	-	dBFS(A)	A-Weighted	
Noise Floor - Mode3, fCLK = 1.536MHz	NF <sub>M3</sub>	-	-102	-	dBFS(A)	A-Weighted	
Noise Floor - LPM, fCLK = 768kHz	NF <sub>LPM</sub>	-	-100	-	dBFS(A)	20Hz to 8kHz bandwidth, A- Weighted	
Total Harmonic Distortion, 94dBSPL	THD <sub>94</sub>	-	0.5	-	%	Measuring 2nd to 5th harmonics 1kHz, all operating modes	
Total Harmonic Distortion, 128dBSPL	THD <sub>128</sub>	-	1.0	-	%	Measuring 2nd to 5th harmonics 1kHz, all operating modes	
Total Harmonic Distortion, 129dBSPL	THD <sub>129</sub>	-	2.0	-	%	Measuring 2nd to 5th harmonics 1kHz, all operating modes	
Total Harmonic Distortion, 130dBSPL	THD <sub>130</sub>	-	10.0	-	%	Measuring 2nd to 5th harmonics 1kHz, all operating modes	
Low Frequency Cutoff Point	f <sub>C_LP</sub>	-	28	-	Hz	-3dB point relative to 1kHz	
-	1			-1		1	

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



### **4 General product characteristics**

 Table 3
 Acoustic specifications (continued)

Parameter	Symbol		Values		Unit	Note or condition
		Min.	Тур.	Max.		
Group Delay, 250Hz	t <sub>gd_250</sub>	-	70	-	μs	
Group Delay, 600Hz	t <sub>gd_600</sub>	-	15	-	μs	
Group Delay, 1kHz	t <sub>gd_1000</sub>	-	6	-	μs	
Group Delay, 4kHz	t <sub>gd_4000</sub>	-	1	-	μs	
hase Response, 5Hz	Φ <sub>75</sub>	-	19	-	0	
Phase Response, LkHz	Φ <sub>1000</sub>	-	2	-	0	
Phase Response, BkHz	Ф <sub>3000</sub>	-	-1	-	0	

Directivity: The device has an omnidirectional pickup pattern.

Polarity: The device has a positive polarity. Positive pressure increases density of 1's, negative pressure decreases density of 1's in data output)

# 4.1.1 Free field frequency response

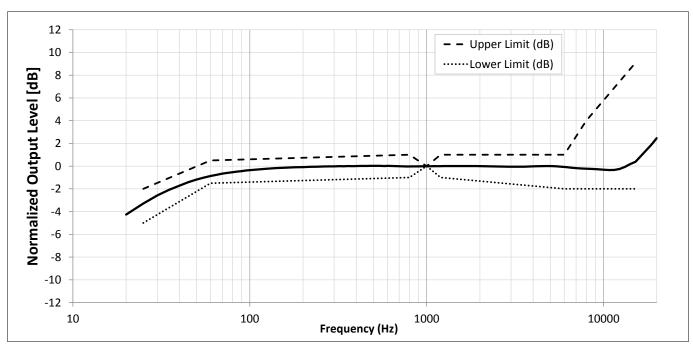


Figure 4 Free field frequency response

#### **IM67D130A**

### AEC-Q103 qualified high performance digital XENSIV MEMS microphone



#### **4 General product characteristics**

Table 4 Free field frequency response, normalized to 1kHz sensitivity value

Frequency (Hz)	Upper Limit (dB)	Lower Limit (dB)
25	-2	-5
60	+0.5	-1.5
800	+1	-1
1000	0	0
1200	+1	-1
6000	+1	-2
8000	+4	-2
15000	+9	-2

#### 4.2 **Electrical parameters and characteristics**

#### **Absolute maximum ratings** 4.2.1

Table 5 **Absolute maximum ratings** 

Parameter	Symbol	Values		Unit	Note or condition	
		Min.	Тур.	Max.		
Voltage on any Pin	V <sub>max</sub>	-	-	4	٧	
Storage Temperature	T <sub>S</sub>	-40	-	125	°C	

Stresses above those listed under "Absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the section "Functional range" of this datasheet is not implied. Furthermore, only single error cases are assumed. More than one stress/error case may also damage the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During absolute maximum rating overload conditions the voltage on V<sub>DD</sub> pins with respect to ground (GND) must not exceed the values defined by the absolute maximum ratings. Lifetime statements are an anticipation based on an extrapolation of Infineon's qualification test results. The actual lifetime of a component depends on its form of application and type of use etc. and may deviate from such statement. Lifetime statements shall in no event extend the agreed warranty period.

### IM67D130A

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



# 4 General product characteristics

# 4.2.2 Functional range

# Table 6 Functional range

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Тур.	Max.		
Supply Voltage	V <sub>DD</sub>	1.62	-	3.60	V	A 100nF bypass capacitor should be placed close to the microphone's V <sub>DD</sub> pin to ensure best SNR performance
Ambient operating temperature	T <sub>A</sub>	-40	-	+105	°C	
Clock Frequency Range, HPM	f <sub>CLK_HPM</sub>	2.9	3.072	3.3	MHz	
Clock Frequency Range, Mode2	f <sub>CLK_M2</sub>	2.1	2.4	2.65	MHz	
Clock Frequency Range, Mode3	f <sub>CLK_M3</sub>	1.05	1.536	1.9	MHz	
Clock Frequency Range, LPM	f <sub>CLK_LPM</sub>	400	768	950	kHz	
Clock Frequency Range, Standby mode	f <sub>CLK_sb</sub>	-	-	250	kHz	DATA = high-Z
PDM Clock Frequency	f <sub>CLK</sub>	0.4	-	3.30	MHz	
VDD Ramp-up Time	V <sub>DD_ru</sub>	-	-	50	ms	Time until V <sub>DD</sub> ≥ V <sub>DD_min</sub>
Clock Duty Cycle	CLK <sub>duty</sub>	40	-	60	%	f <sub>CLK</sub> < 2.65MHz
Clock Duty Cycle, High performance mode	CLK <sub>duty_HPM</sub>	48	-	52	%	f <sub>CLK</sub> ≥ 2.9MHz
Clock Rise/Fall Time	t <sub>CR</sub> / t <sub>CF</sub>	-	-	13	ns	
Input Logic Low Level	V <sub>IL</sub>	-0.3	-	0.35xV <sub>DD</sub>	V	
Input Logic High Level	V <sub>IH</sub>	0.65xV <sub>DD</sub>	-	V <sub>DD</sub> +0.3	V	
Output Load Capacitance on DATA	C <sub>load</sub>	-	-	200	pF	

# 4.2.3 Electrical characteristics

Test conditions (unless otherwise specified in the table):  $V_{DD}$  = 1.8V  $\pm$  0.1V,  $T_A$  = 25°C  $\pm$  5°C

## IM67D130A

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



# 4 General product characteristics

#### **General electrical characteristics** Table 7

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Тур.	Max.	1	
Current Consumption, HPM	I <sub>DD_HPM</sub>	-	980	1300	μΑ	No load on DATA
Current Consumption, Mode2	I <sub>DD_M2</sub>	-	800	1050	μΑ	No load on DATA
Current Consumption, Mode3	I <sub>DD_M3</sub>	-	620	800	μΑ	No load on DATA
Current Consumption, LPM	I <sub>DD_LPM</sub>	-	300	380	μΑ	No load on DATA
Current Consumption, Standby mode	I <sub>standby</sub>	-	25	50	μΑ	No load on DATA
Current Consumption, Clock off mode	I <sub>clock_off</sub>	-	-	1	μА	CLOCK pulled low
Short Circuit Current	I <sub>short</sub>	1	-	20	mA	Grounded DATA pin
Power Supply Rejection	PSR <sub>1k_NM</sub>	-	-80	-	dBFS	100mV <sub>pp</sub> sine wave on V <sub>DD</sub> swept from 200Hz to 20kHz
Power Supply Rejection	PSR <sub>217_NM</sub>	-	-86	-	dBFS(A)	$100 \text{mV}_{\text{rms}}$ , 217Hz square wave on $V_{\text{DD}}$ , A-weighted
Startup Time, ±0.5dB sensitivity accuracy	t <sub>start-up</sub>	-	-	20	ms	Time to start up in all operating modes after V <sub>DD_min</sub> and CLOCK have been applied
Startup Time, ±0.2dB sensitivity accuracy	t <sub>start-up_HP</sub>	-	-	50	ms	Time to start up in all operating modes after V <sub>DD_min</sub> and CLOCK have been applied
Mode Switch Time, ±0.5dB sensitivity accuracy	t <sub>mode-switch</sub>	-	-	20	ms	Time to switch between operating modes. V <sub>DD</sub> remains on during the mode switch
Mode Switch Time, ±0.2dB sensitivity accuracy	t <sub>mode-</sub> switch_HP	-	-	50	ms	Time to switch between operating modes. V <sub>DD</sub> remains on during the mode switch
Hysteresis Width	V <sub>hys</sub>	0.1xV <sub>DD</sub>	-	0.29xV <sub>DD</sub>	V	
Output Logic Low Level	V <sub>OL</sub>	-	-	0.3xV <sub>DD</sub>	V	I <sub>out</sub> = 2mA
Output Logic High Level	V <sub>OH</sub>	0.7xV <sub>DD</sub>	-	-	V	I <sub>out</sub> = 2mA

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



## **4 General product characteristics**

Table 7 General electrical characteristics (continued)

Parameter	Symbol		Values			Note or condition
		Min.	Тур.	Max.		
Delay Time for DATA Driven	t <sub>DD</sub>	40	-	80	ns	Delay time from CLOCK edge (0.5xV <sub>DD</sub> ) to DATA driven
Delay Time for DATA High-Z	t <sub>HZ</sub>	5	-	30	ns	Delay time from CLOCK edge (0.5xV <sub>DD</sub> ) to DATA high impedance state <sup>1)</sup>
Delay Time for DATA Valid	t <sub>DV</sub>	-	-	100	ns	Delay time from CLOCK edge (0.5xV <sub>DD</sub> ) to DATA valid (<0.3xV <sub>DD</sub> or >0.7xV <sub>DD</sub> ) <sup>2)</sup>

 $<sup>1) \</sup>hspace{0.5cm} t_{HZ} \hspace{0.1cm} \text{is dependent upon $C_{load}$} \\$ 

# 4.2.4 Timing diagram

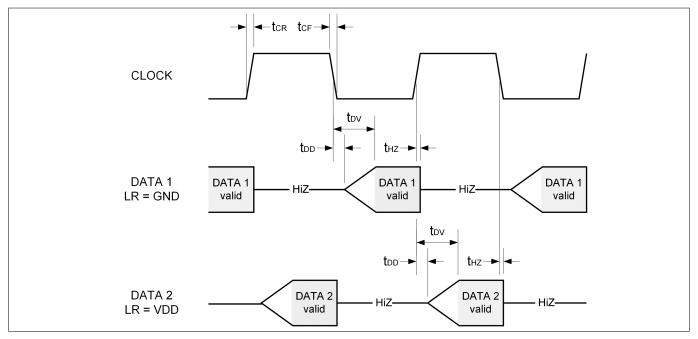


Figure 5 Timing diagram

<sup>2)</sup> Load on DATA:  $C_{load} = 100 pF$ ,  $R_{load} = 100 k\Omega$ 

#### **AEC-Q103 qualified high performance digital XENSIV MEMS microphone**



### **5 Application information**

#### **Application information** 5

#### **5.1 Use cases**

- Total Harmonic Distortion (THD) below 1% up to high sound pressure levels (SPL)
  - Clear speech even with high wind
  - Reliable voice commands during high background noise
  - Effective active noise cancellation even close to loud noise source
- High Signal to Noise Ratio (SNR)
  - Far field audio signal pick-up
  - Low volume audio and whispered voice capturing
  - Good performance with speech recognition algorithms
  - Microphone noise is no longer limiting the audio chain
- Close sensitivity and phase matching
  - Good performance in audio beamforming
  - High and precise attenuation of background noise
  - Full utilization of voice algorithms capability
- Flat frequency response with low f<sub>C LP</sub> (low frequency cutoff point) and small group delay
  - Good performance in active noise cancellation systems
  - Excellent speech quality over full frequency range
- Power optimized modes
  - Low current consumption for always on applications
  - Long operating time of battery powered devices

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



## **5 Application information**

#### Typical stereo application circuit **5.2**

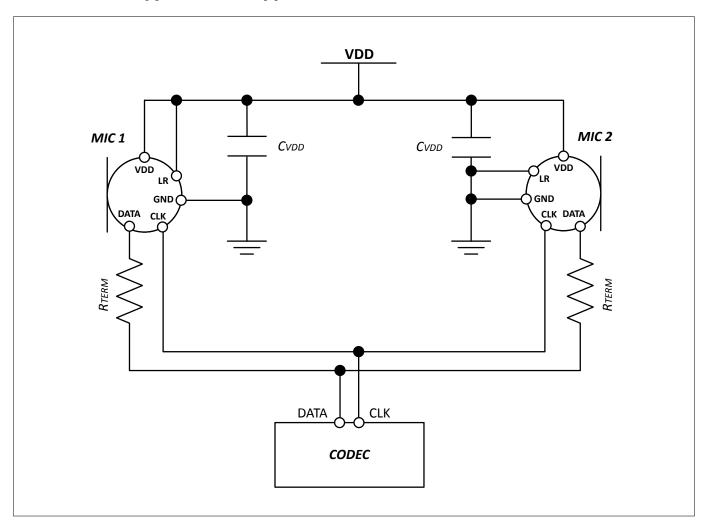


Figure 6 Typical stereo application circuit

Note:

For best performance it is strongly recommended to place a 100nF ( $C_{\text{VDD\_typical}}$ ) capacitor between  $V_{\rm DD}$  and ground. The capacitor should be placed as close to  $V_{\rm DD}$  as possible. A termination resistor  $(R_{\mathsf{TERM}})$  of about 100 $\Omega$  may be added to reduce the ringing and overshoot on the output signal.

### **AEC-Q103 qualified high performance digital XENSIV MEMS microphone**



#### **6 Package information**

#### **Package information** 6

This product is compliant to RoHS

#### **Package outline** 6.1

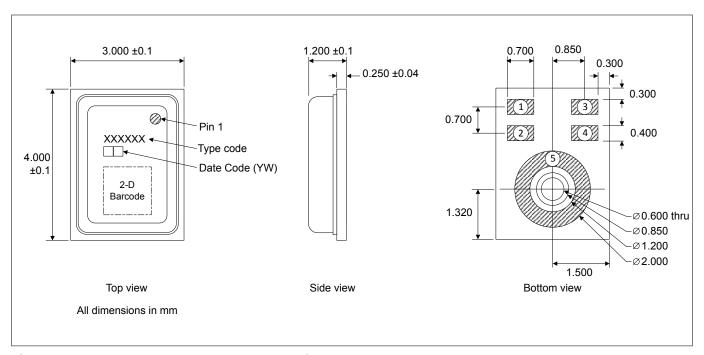


Figure 7 PG-LLGA-5-1 package drawing

#### 6.2 Footprint and stencil recommendation

The acoustic port hole diameter in the PCB should be larger than the acoustic port hole diameter of the MEMS Microphone to ensure optimal performance. A PCB sound port size of radius 0.4 mm (diameter 0.8mm) is recommended.

The board pad and stencil aperture recommendations shown in the figure below are based on Solder Mask Defined (SMD) pads. The specific design rules of the board manufacturer should be considered for individual design optimizations or adaptations.

### AEC-Q103 qualified high performance digital XENSIV MEMS microphone



### **6 Package information**

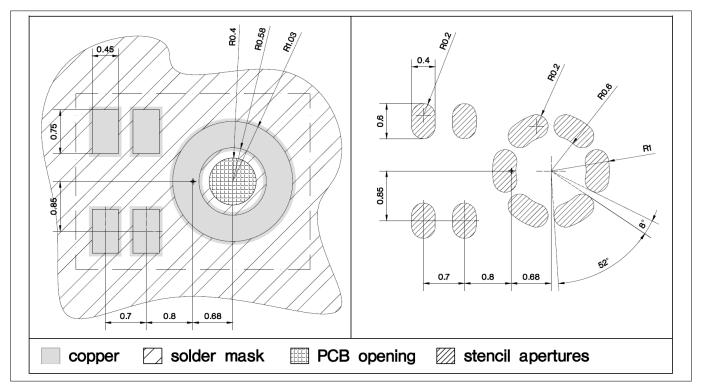


Figure 8 PG-LLGA-5-1 footprint and stencil recommendation

Dimensions are in millimeters unless otherwise specified. Note:

More information can be found on the Infineon website:

https://www.infineon.com/cms/en/product/packages/PG-LLGA/PG-LLGA-5-1/

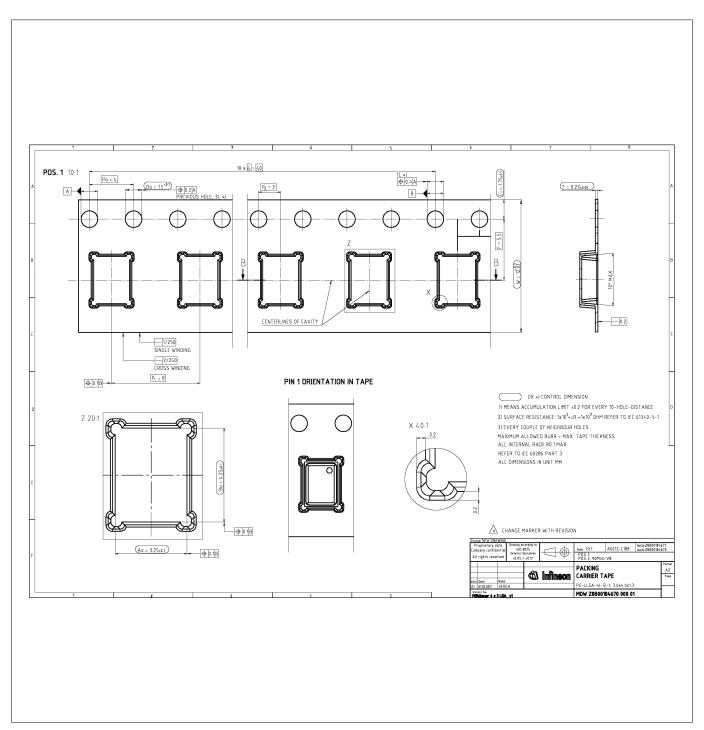
#### **Packing** 6.3

For shipping and assembly the Infineon microphones are packed in product specific tape-and-reel carriers. A detailed drawing of the carrier can be seen in the figure below.

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



### **6 Package information**



**PG-LLGA-5-1 tape dimensions** 

More information can be found on the Infineon website:

https://www.infineon.com/cms/en/product/packages/PG-LLGA/PG-LLGA-5-1/

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



7 Reliability specifications

# 7 Reliability specifications

The microphone sensitivity after stress and over temperature does not deviate by no more than +/- 3dB from the initial value.

Table 8 Qualification tests according to AEC-Q103-003

Test	Stress condition	Standard
Temperature humidity bias	T <sub>A</sub> = +85°C, R.H. = 85%, V <sub>DD</sub> = 3.6V, cyclical bias, 1000 hours	AEC Q100 Rev.H.
Temperature humidity storage	T <sub>A</sub> = +85°C, R.H = 85%, 1000 hours	AEC Q100 Rev.H.
Temperature cycling	T <sub>A</sub> = -55°C +125°C, 30 min cycle time, 1000 hours	AEC Q100 Rev.H.
High temperature storage life	T <sub>A</sub> = +125°C, 1000 hours	AEC Q100 Rev.H.
High temperature operating life	T <sub>A</sub> = +125°C, V <sub>DD</sub> = 3.6V, 1000 hours	AEC Q100 Rev.H.
Early life failure rate	T <sub>A</sub> = +125°C, V <sub>DD</sub> = 3.6V, 1000 hours Read out after stress at room temperature	AEC Q100 Rev.H.
Wire bond shear	Bump shear test	AEC Q100-001
Wire bond pull	-	MIL-STD883 Method 2011
Solderability	-	JESD22-B102
Physical dimensions	-	JESD22-B100 and B108
Solder ball shear	-	AEC Q103-003
Mechanical shock	3 pulses, 0.5msec duration, 10,000g peak acceleration in x,y and z planes	JESD22-B104
Variable frequency vibration	20Hz to 2kHz to 20Hz (logarithmic variation) in 12 minutes, 4x in each orientation, 20g peak acceleration	JESD22-B103
Package drop	10x on each of 6 axes (60 drops total) from a high of 1.2m onto a concrete surface	TBD
Die shear	-	MIL-STD-883 Method 2019
Humidity and temperature cycle	5 cycles (24h/cycle)	IEC 60068-2-38
Low temperature operating life	T <sub>A</sub> = -40°C, V <sub>DD</sub> = 3.6V, 1000 hours	JESD22-A108
Low temperature storage	T <sub>A</sub> = -40°C, V <sub>DD</sub> = 3.6V, 1000 hours	JESD22-A119
Endurance life test	96 hours at 130dB continuous signal	AEC Q103-003
Electrostatic discharge, Human body model (HBM)	all pins, U <sub>ESD</sub> = ±2000V	EIA/JESD22/A114
Electrostatic discharge, Charged device model (CDM)	all pins, U = ±500V	ESD STM 5.3.1
Latch-up	T <sub>A</sub> = 105°C, I = ±200mA	AEC Q100 Rev.H.

## IM67D130A

# AEC-Q103 qualified high performance digital XENSIV MEMS microphone



8 Revision history

#### **Revision history** 8

#### **Revision history** Table 9

Document version	Date of release	Description of changes
0.1	17.07.2020	Initial release
0.2	02.09.2020	<ul> <li>First release of IM67D130A</li> <li>Structure and content adapted to ATV rules</li> <li>update of SNR</li> <li>AEC-Q103 qualification added</li> </ul>
0.3	14.12.2020	<ul> <li>Editorial changes</li> <li>Table 2: Pin name changed</li> <li>Symbols added and modified in several EC-tables</li> <li>Table 8: ESD and LU tests added</li> </ul>

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